



US 20230230962A1

(19) **United States**

(12) **Patent Application Publication**  
**Yu et al.**

(10) **Pub. No.: US 2023/0230962 A1**

(43) **Pub. Date: Jul. 20, 2023**

(54) **3D INTEGRATED CIRCUIT (3DIC)  
STRUCTURE**

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(21) Appl. No.: **18/190,341**

(22) Filed: **Mar. 27, 2023**

**Related U.S. Application Data**

(60) Continuation of application No. 17/649,381, filed on Jan. 31, 2022, which is a division of application No. 16/435,697, filed on Jun. 10, 2019, now Pat. No. 11,239,201, which is a division of application No. 14/591,784, filed on Jan. 7, 2015, now Pat. No. 10,319,701.

**Publication Classification**

(51) **Int. Cl.**  
**H01L 25/065** (2006.01)  
**H01L 25/00** (2006.01)  
**H01L 23/00** (2006.01)

(52) **U.S. Cl.**

CPC ..... **H01L 25/0657** (2013.01); **H01L 25/50**  
(2013.01); **H01L 24/81** (2013.01); **H01L 24/05**  
(2013.01); **H01L 24/16** (2013.01); **H01L**  
**2224/81007** (2013.01); **H01L 2224/81801**  
(2013.01); **H01L 2224/81948** (2013.01); **H01L**  
**2224/81947** (2013.01); **H01L 2225/06513**  
(2013.01); **H01L 2225/06541** (2013.01); **H01L**  
**2224/13147** (2013.01); **H01L 24/13** (2013.01);  
**H01L 2224/11462** (2013.01); **H01L**  
**2224/05571** (2013.01); **H01L 2924/381**  
(2013.01); **H01L 2224/13101** (2013.01); **H01L**  
**2224/1607** (2013.01); **H01L 2224/16225**  
(2013.01); **H01L 2224/16145** (2013.01); **H01L**  
**2224/81141** (2013.01); **H01L 2224/11464**  
(2013.01); **H01L 2224/1147** (2013.01); **H01L**  
**2224/81815** (2013.01); **H01L 2924/14**  
(2013.01); **H01L 2224/05558** (2013.01)

(57)

**ABSTRACT**

An embodiment bonded integrated circuit (IC) structure includes a first IC structure and a second IC structure bonded to the first IC structure. The first IC structure includes a first bonding layer and a connector. The second IC structure includes a second bonding layer bonded to and contacting the first bonding layer and a contact pad in the second bonding layer. The connector extends past an interface between the first bonding layer and the second bonding layer, and the contact pad contacts a lateral surface and a sidewall of the connector.

